

IN THE CLAIMS

Amend claims 1, 5, 8 and 9; and add new claims 32-35 as follows:

1. (Currently Amended) A semiconductor device comprising:

surface mounted parts;

a first substrate on which the surface mounted parts are mounted by ~~first~~ soldering;

solder connection portions for connecting the surface mounted parts to the wiring substrate; and

a sealing portion formed with an elastic insulative resin for covering the surface mounted parts and the solder connection portions,

wherein the elastic resin is a resin having a modulus of elasticity of 1 MPa to 200 MPa at a temperature of 150°C or higher, ~~and~~

~~wherein the semiconductor device is mounted on a second substrate by second soldering.~~

2. (Canceled).

3. (Previously Presented) A semiconductor device according to claim 1, wherein the elastic resin is a resin having a modulus of elasticity of 1 MPa to 200 MPa at a temperature of 25°C.

4. (Canceled).

5. (Currently Amended) A semiconductor device comprising:

surface mounted parts;

a wiring substrate on which the surface mounted parts are mounted by ~~first~~ soldering;

solder connection portions for connecting the surface mounted parts to the wiring substrate; and

a sealing portion formed with a silicone resin which is an elastic insulative resin for covering the surface mounted parts and the solder connection portions, wherein the silicone resin has a modulus of elasticity of 1 to 200 MPa at a temperature of 150°C or higher,

~~wherein the semiconductor device is mounted on a substrate by second soldering.~~

6. (Original) A semiconductor device according to claim 1, wherein the elastic resin is a silicone resin.

7. (Original) A semiconductor device according to claim 1, wherein the elastic resin is an epoxy resin.

8. (Currently Amended) A semiconductor device comprising:

semiconductor chips which are surface mounted parts each formed with a surface electrode at its main surface;

chip parts which are surface mounted parts each formed with connection terminals on both ends;

a module substrate which is a wiring substrate on which the semiconductor chips and the chip parts are mounted by ~~first~~ soldering;

solder connection portions for connecting the chip parts to the wiring substrate; and

a sealing portion formed with a silicone resin which is an elastic insulative resin for covering the semiconductor chips, the chip parts and the solder connection portions, wherein the silicone resin has a modulus of elasticity of 1 to 200 MPa at a temperature of 150°C or higher,

~~wherein the semiconductor device is mounted on a substrate by second soldering.~~

9. (Currently Amended) A semiconductor device comprising:

semiconductor chips which are surface mounted parts formed with a surface electrode at the main surface;

chip parts which are surface mounted parts each formed with connection terminals on both ends;

a module substrate which is a wiring substrate on which the semiconductor chips and the chip parts are mounted by ~~first~~ soldering;

solder connection portions for connecting the chip parts to the wiring substrate; and

a sealing portion formed with an insulative resin having a modulus of elasticity of 1 MPa to 200 MPa at a

temperature of 150°C or more and a modulus of elasticity of 200 MPa or more at a temperature of 25°C for covering the semiconductor chips, the chip parts and the solder connection portions,

~~_____ wherein the semiconductor device is mounted on a substrate by second soldering.~~

10. (Original) A semiconductor device according to claim 9, wherein the insulative resin is an epoxy resin.

11. (Previously Presented) A semiconductor device according to claim 10, wherein the chip parts are mounted by the first soldering to the substrate terminals each formed with a gold plating layer, Sn plating layer or Pb-Sn series solder plating layer at the surface.

12. (Original) A semiconductor device according to claim 11, wherein the surface electrodes of the semiconductor chips are wire bonded by gold wires to the substrate terminals each formed with a gold plating layer, with a Sn plating layer or a Pb-Sn series solder plating layer at the surface.

13. (Original) A semiconductor device according to claim 11, wherein the main surface of the semiconductor chips and the surface of the wiring substrate on the side of supporting the chips are opposed to each other and the surface electrodes of the semiconductor chip and the substrate terminals each formed with a gold metal layer, an Sn plating layer or a Pb-Sn series solder plating layer at the surface are connected by way of gold bumps or solder bumps.

14. (Previously Presented) A semiconductor device according to claim 12, wherein the semiconductor chips and the chip parts are mounted on a rectangular module substrate as said module substrate, and the wire loops of the gold wires are formed in a direction parallel with a longitudinal direction of the module substrate.

15-31. (Canceled).

32. (New) A semiconductor device according to claim 1, wherein the surface mounted parts are mounted by first

soldering and the semiconductor device is mounted on a second substrate by second soldering.

33. (New) A semiconductor device according to claim 5, wherein the surface mounted parts are mounted by first soldering and the semiconductor device is mounted on a second substrate by second soldering.

34. (New) A semiconductor device according to claim 8, wherein the semiconductor chips and the chip parts are mounted by first soldering and the semiconductor device is mounted on a second substrate by second soldering.

35. (New) A semiconductor device according to claim 9, wherein the semiconductor chips and the chip parts are mounted by first soldering and the semiconductor device is mounted on a second substrate by second soldering.